

Editorial



It is my great pleasure to announce the publication of a special JSTS issue on the 14th Korean Conference on Semiconductors (KCS 2007) held in Jeju, from February 8 to 9, 2007. Among the 511 outstanding papers presented at the conference, 6 papers have been chosen by a committee to be published in the special issue of JSTS.

The first paper is “A Sense Amplifier Scheme with Offset Cancellation for Giga-bit DRAM” in the section of Memory Design. 2nd and 3rd paper are “Threshold Voltage Modeling of Double-Gate MOSFETs by Considering Barrier Lowering” and “Influences of Trap States at Metal/Semiconductor Interface on Metallic Source/Drain Schottky-Barrier MOSFET” in the section of Nano-Science and Technology. 4th paper is “A New Noise Parameter Model of RF MOSFETs” in the section of Device Technology, CMOS & Interconnect Reliability, Simulation & Modeling. 5th and 6th paper are “PWM/PFM Dual Mode SMPS Controller IC for Active Forward Clamp and LLC Resonant Converters” and “A Fully Integrated 5-GHz CMOS Power Amplifier for 802.11a WLAN Applications” in the section of Analog Design.

I would like to express my gratitude to all the authors for submitting these excellent papers.

Jong-Sung Lim
Guest editor of this special issue

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